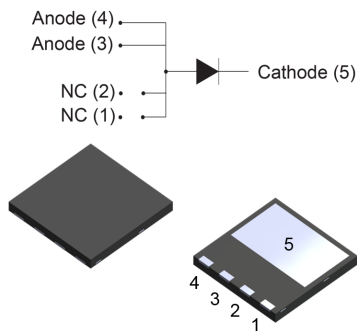


## 650 V power Schottky silicon carbide diode



PowerFLAT 8x8 HV



## Features

- Less than 1 mm height package
- High creepage package
- No or negligible reverse recovery
- Temperature independent switching behavior
- High forward surge capability
- Low drop forward voltage
- Power efficient product
- ECOPACK2 compliant component

## Applications

- Switch mode power supply
- Boost PFC
- Bootstrap diode
- LLC clamping function
- High frequency inverter applications

## Description

This 8 A, 650 V, SiC diode is an ultra-high performance power Schottky diode. It is manufactured using a silicon carbide substrate. The wide band gap material allows the design of a Schottky diode structure with a 650 V rating. Due to the Schottky construction, no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature.

Qualified in low profile package, the STPSC8H065DLF in PowerFLAT 8x8 HV, enables low drop forward voltage associated to high surge capabilities in low space environment such as telecom and network, industrial or renewable energy domains.

## Product status link

[STPSC8H065DLF](#)

## Product summary

Symbol	Value
$I_{F(AV)}$	8 A
$V_{RRM}$	650 V
$V_{F(typ.)}$	1.38 V
$T_{j(max.)}$	175 °C

## Product label



# 1 Characteristics

**Table 1. Absolute ratings (limiting values at 25 °C unless otherwise specified)**

Symbol	Parameter		Value	Unit
$V_{RRM}$	Repetitive peak reverse voltage	$T_j = -40\text{ °C to } +175\text{ °C}$	650	V
$I_{F(RMS)}$	Forward rms current		22	A
$I_{F(AV)}$	Average forward current	$T_c = 135\text{ °C}^{(1)}$ , DC	8	A
$I_{FSM}$	Surge non repetitive forward current	$t_p = 10\text{ ms sinusoidal}$ , $T_c = 25\text{ °C}$	75	A
		$t_p = 10\text{ ms sinusoidal}$ , $T_c = 125\text{ °C}$	69	
		$t_p = 10\text{ }\mu\text{s square}$ , $T_c = 25\text{ °C}$	800	
$I_{FRM}$	Repetitive peak forward current	$T_c = 135\text{ °C}^{(1)}$ , $T_j = 175\text{ °C}$ , $\delta = 0.1$	32	A
$T_{stg}$	Storage temperature range		-55 to +175	°C
$T_j$	Operating junction temperature range		-40 to +175	°C

1. Value based on  $R_{th(j-c)}$  max.

**Table 2. Thermal resistance parameters**

Symbol	Parameter	Typ. value	Max. value	Unit
$R_{th(j-c)}$	Junction to case	1.7	2.5	°C/W

**Table 3. Static electrical characteristics**

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
		$T_j$	$V_R$				
$I_R^{(1)}$	Reverse leakage current	$T_j = 25\text{ °C}$	$V_R = V_{RRM}$	-	7	80	$\mu\text{A}$
		$T_j = 150\text{ °C}$		-	65	335	
$V_F^{(2)}$	Forward voltage drop	$T_j = 25\text{ °C}$	$I_F = 8\text{ A}$	-	1.38	1.55	V
		$T_j = 150\text{ °C}$		-	1.60	1.95	

1.  $t_p = 10\text{ ms}$ ,  $\delta < 2\%$

2.  $t_p = 500\text{ }\mu\text{s}$ ,  $\delta < 2\%$

To evaluate the conduction losses, use the following equation:

$$P = 1.00 \times I_{F(AV)} + 0.119 \times I_{F(RMS)}^2$$

For more information, please refer to the following application notes related to the power losses:

- AN604 : Calculation of conduction losses in a power rectifier
- AN4021 : Calculation of reverse losses on a power diode

**Table 4. Dynamic electrical characteristics**

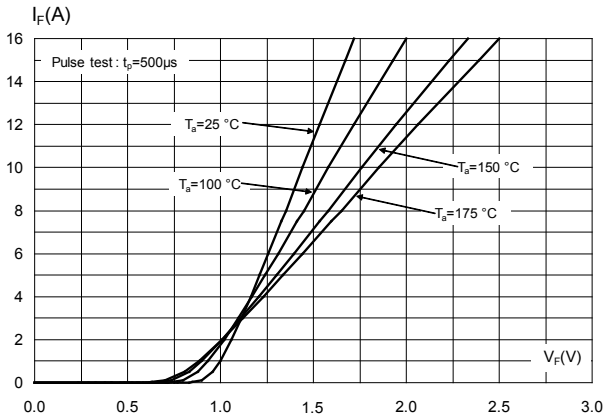
Symbol	Parameter	Test conditions	Typ.	Unit
$Q_{cj}$	Total capacitive charge	$V_R = 400\text{ V}$	26	nC
$C_j$	Total capacitance	$V_R = 0\text{ V}, T_c = 25\text{ }^\circ\text{C}, F = 1\text{ MHz}$	460	pF
		$V_R = 400\text{ V}, T_c = 25\text{ }^\circ\text{C}, F = 1\text{ MHz}$	46	

1. Most accurate value for the capacitive charge:

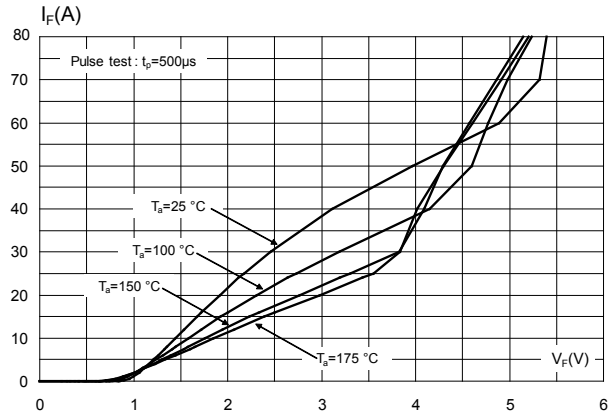
$$Q_{cj}(V_R) = \int_0^{V_R} C_j(V) dV$$

### 1.1 Characteristics (curves)

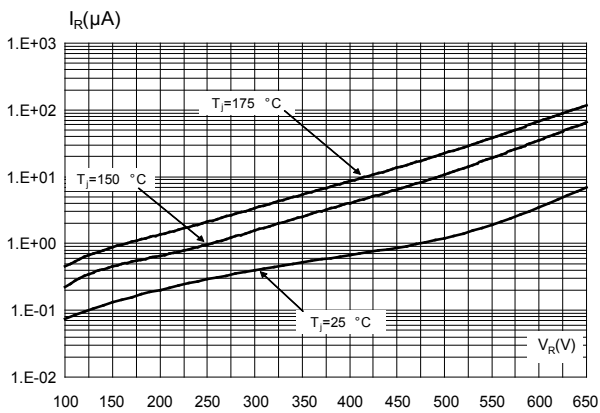
**Figure 1. Forward voltage drop versus forward current (typical values, low level)**



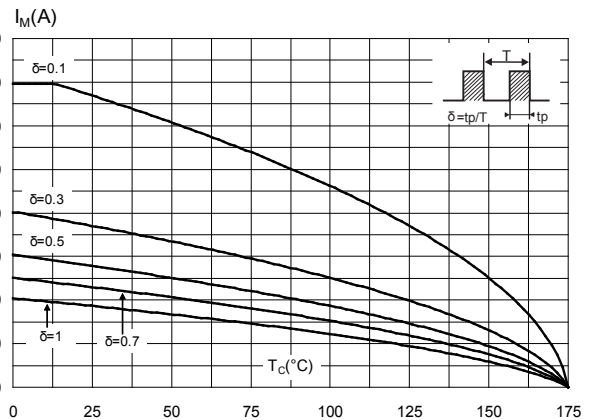
**Figure 2. Forward voltage drop versus forward current (typical values, high level)**



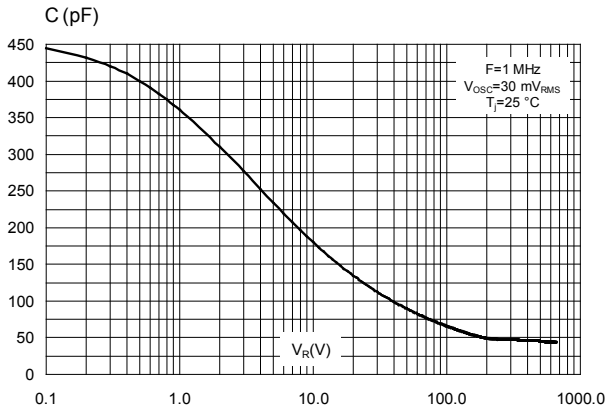
**Figure 3. Reverse leakage current versus reverse voltage applied (typical values)**



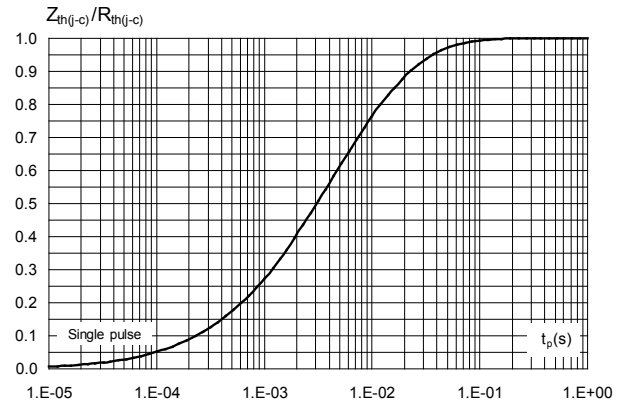
**Figure 4. Peak forward current versus case temperature**



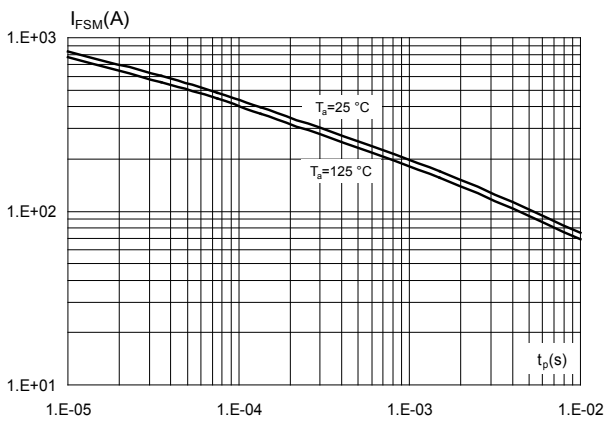
**Figure 5. Junction capacitance versus reverse voltage applied (typical values)**



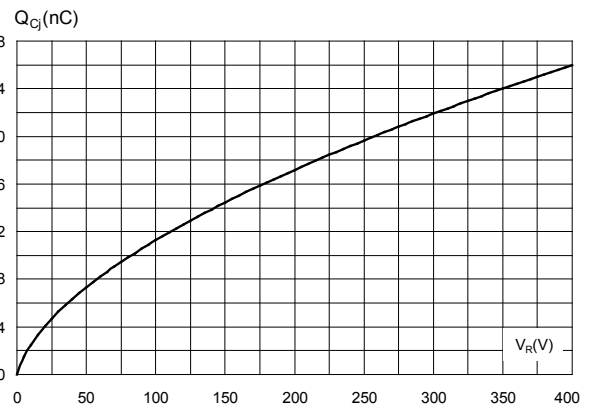
**Figure 6. Relative variation of thermal impedance junction to case versus pulse duration**



**Figure 7. Non-repetitive peak surge forward current versus pulse duration (sinusoidal waveform)**



**Figure 8. Total capacitive charges versus reverse voltage applied (typical values)**



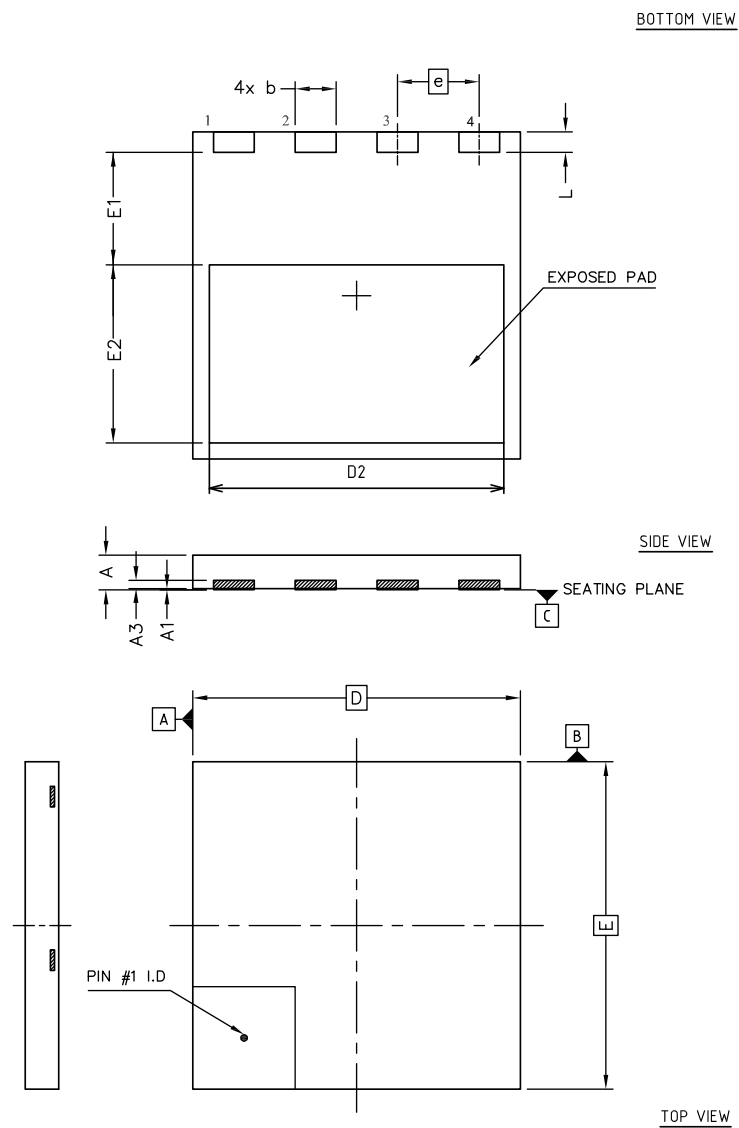
## 2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

### 2.1 PowerFLAT 8x8 HV package information

- Epoxy meets UL94, V0
- Lead-free Package

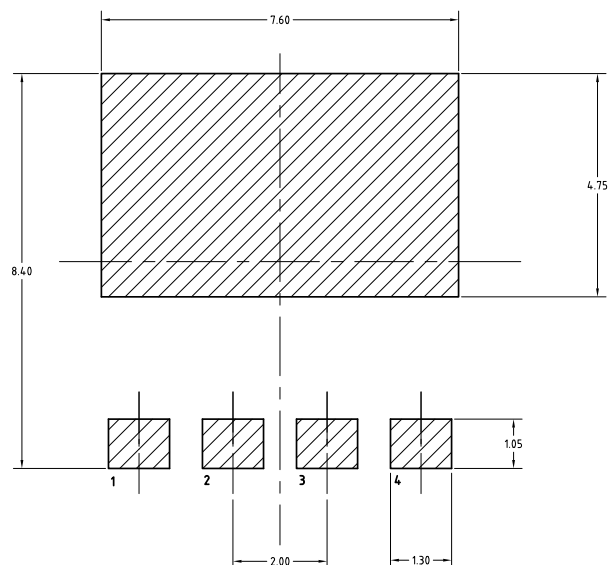
**Figure 9. PowerFLAT 8x8 HV package outline**



**Table 5. PowerFLAT 8x8 HV mechanical data**

Ref.	Dimensions (in mm)		
	Min.	Typ.	Max.
A	0.75	0.85	0.95
A1	0.00		0.05
A3	0.10	0.20	0.30
b	0.90	1.00	1.10
D	7.90	8.00	8.10
E	7.90	8.00	8.10
D2	7.10	7.20	7.30
E1	2.65	2.75	2.85
E2	4.25	4.35	4.45
e	2.00		
L	0.40	0.50	0.60

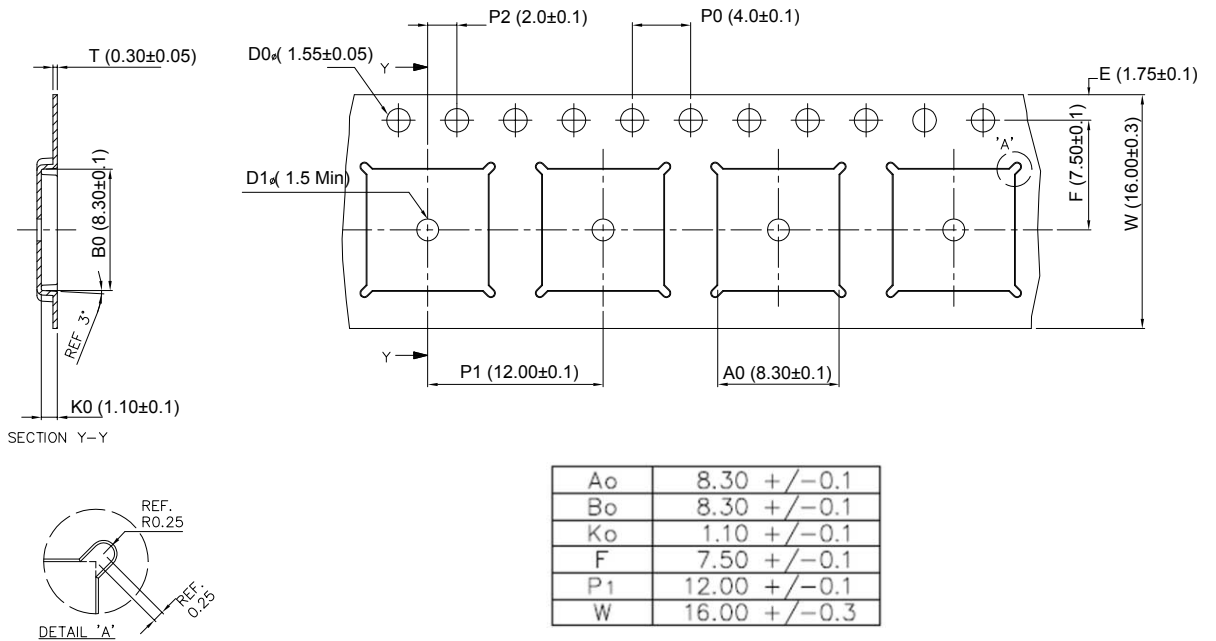
**Figure 10. PowerFLAT 8x8 HV footprint**



*Note:* All dimensions are in millimeters.

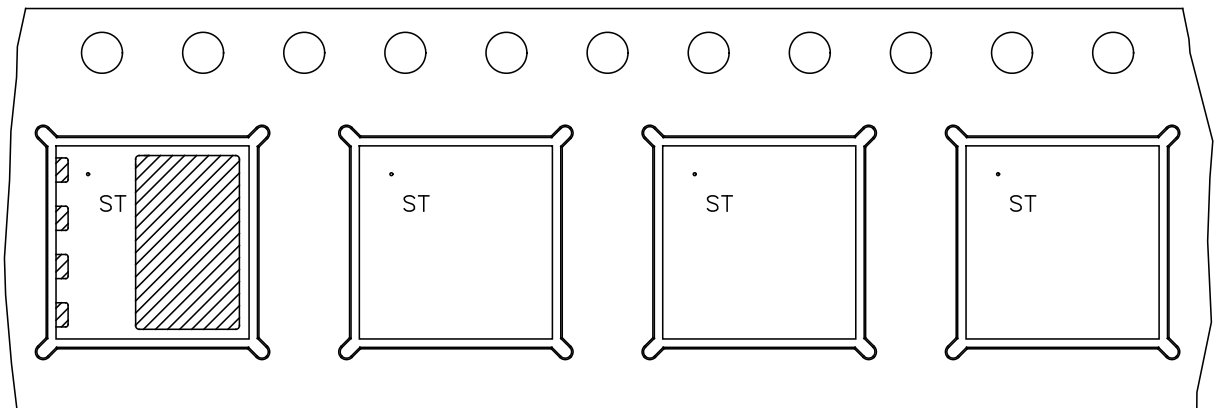
## 2.2 PowerFLAT 8x8 HV packing information

Figure 11. PowerFLAT 8x8 HV tape



Note: All dimensions are in millimeters.

Figure 12. PowerFLAT 8x8 HV package orientation in carrier tape







### 3 Ordering Information

**Table 6. Ordering information**

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STPSC8H065DLF	PSC8H065	PowerFLAT 8x8 HV	170 mg	3000	Reel

## Revision history

**Table 7. Document revision history**

Date	Version	Changes
29-Nov-2018	1	Initial release.
31-Mar-2021	2	Inserted STPOWER logo and updated <a href="#">Table 6</a> .

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